



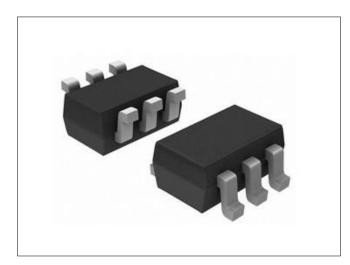
# Product data sheet

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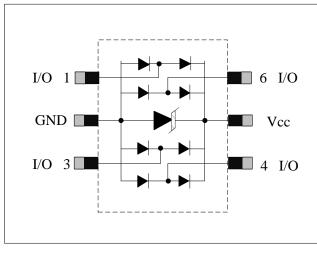


NUP4202W1T2G-MS HF 🗹

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# Schematic & PIN Configuration



SOT363

#### Features

- 100Watts peak pulse power (tp =  $8/20\mu s$ )
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low capacitance (Cj=0.30pF typ.)
- Protection one data/power line to:
- IEC 61000-4-2  $\pm$ 12kV contact  $\pm$ 15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20μs)

# Applications

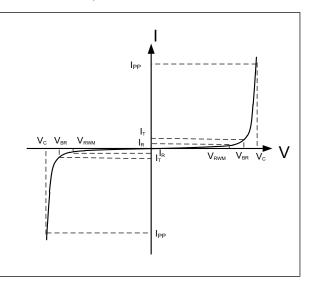
- Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

#### **Mechanical Data**

- SOT363 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

#### Electrical Parameters (TA = 25 °C unless otherwise noted)

Symbol	Parameter
Ipp	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
VRWM	Working Peak Reverse Voltage
Ir	Maximum Reverse Leakage Current @ VRWM
VBR	Breakdown Voltage @ IT
Іт	Test Current



Note:.  $8/20\mu s$  pulse waveform.



### **Absolute Maximum Rating**

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Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20 \mu s$ )	$P_{PP}$	100	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ ) (note1)	I <sub>pp</sub>	5.0	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	15 12	kV
Lead Soldering Temperature	$T_L$	260(10seconds)	°C
Junction Temperature	TJ	-55 to + 125	°C
Storage Temperature	T <sub>stg</sub>	-55 to + 125	°C

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V <sub>RWM</sub>				5.0	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA	6			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V,T=25°C			1	uA
Peak Pulse Current	I <sub>PP</sub>	tp =8/20µs			5	А
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> =5.0A,t <sub>p</sub> =8/20µs		12	18	V
Interview Constitution	Cj	$V_R = 0V, f = 1MHz$ IO to IO		0.3	0.45	pF
Junction Capacitance		$V_R = 0V, f = 1MHz$ IO to GND			0.9	

Fig.1 Peak Pulse Power Rating Curve

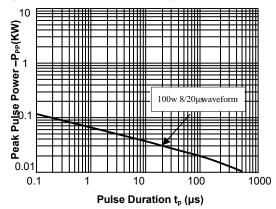


Fig.3 Pulse Waveform-8/20µs

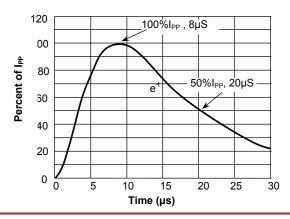


Fig.2 Pulse Derating Curve

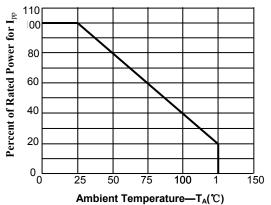
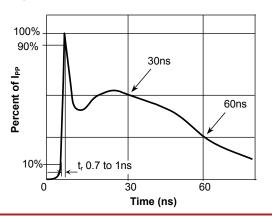
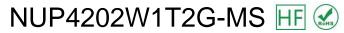


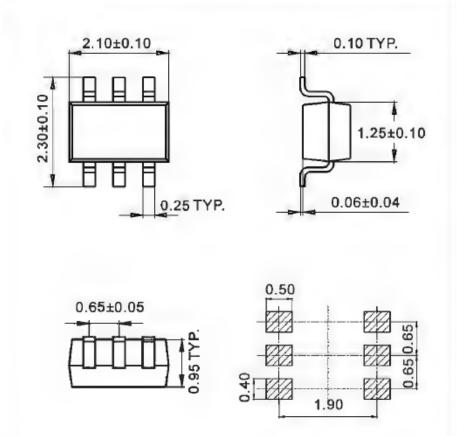
Fig.4 Pulse Waveform-ESD(IEC61000-4-2)







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#### **REEL SPECIFICATION**

P/N	PKG	QTY
NUP4202W1T2G-MS	SOT-363	3000



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